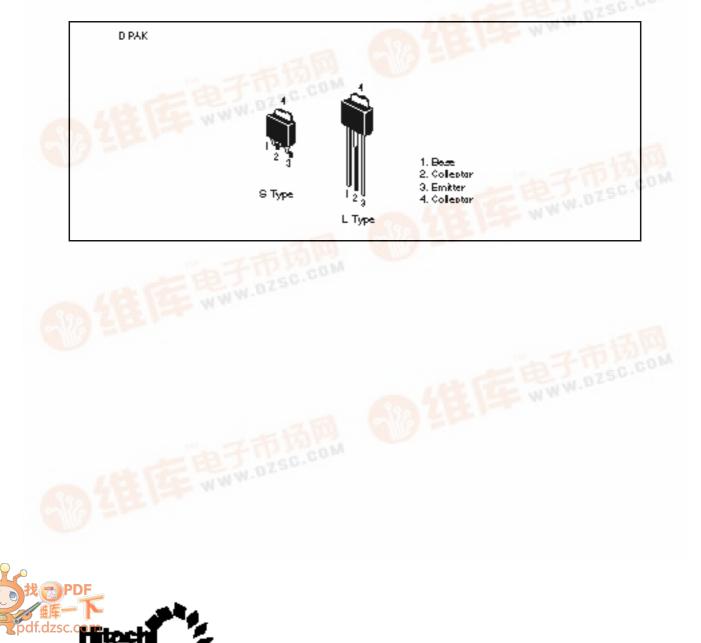
Silicon NPN Epitaxial

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Application

WWW.DZS Low frequency power amplifier complementary pair with 2SB1409(L)/(S)

Outline



Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

		Ratings				
Item	Symbol	2SD2122(L)/(S	2SD2123(L)/(S)	Unit		
Collector to base voltage	V _{CBO}	180	180	V		
Collector to emitter voltage	V _{CEO}	120	160	V		
Emitter to base voltage	V_{EBO}	5	5	V		
Collector current	Ι _c	1.5	1.5	А		
Collector peak current	I _{C(peak)}	3	3	А		
Collector power dissipation	P _c * ¹	18	18	W		
Junction temperature	Tj	150	150	°C		
Storage temperature	Tstg	-55 to +150	–55 to +150	°C		
Noto: 1 Value at T = 25°C						

Note: 1. Value at $T_c = 25^{\circ}C$.

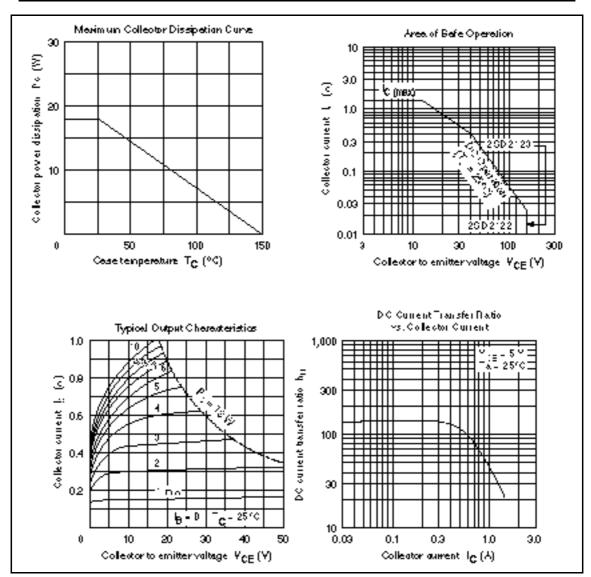
Electrical Characteristics (Ta = 25°C)

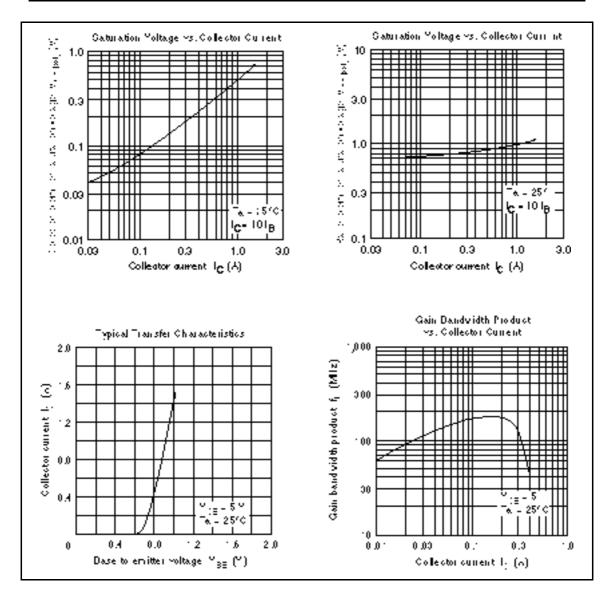
		2SD2	122(L)	/(S)	2SD2123(L)/(S)		SD2123(L)/(S)		
Item	Symbol	Min	Тур	Max	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{\rm (BR)CBO}$	180	_	_	180	_		V	$I_{c} = 1 \text{ mA}, I_{E} = 0$
Collector to emitter breakdown voltage	$V_{\rm (BR)CEO}$	120	_	_	160	_	_	V	I_c = 10 mA, $R_{_{BE}}$ =
Emitter to base breakdown voltage	$V_{\rm (BR)EBO}$	5	_	_	5	_	_	V	$I_{\rm E} = 1$ mA, $I_{\rm C} = 0$
Collector cutoff current	I _{CBO}	_	—	10	_	—	10	μA	$V_{CB} = 160 \text{ V}, \text{ I}_{E} = 0$
DC current transfer ratio	$h_{\rm FE1}^{*2}$	60	—	200	60	—	200	А	$V_{ce} = 5 \text{ V}, \text{ I}_{c} = 150 \text{ mA}^{*1}$
	\mathbf{h}_{FE2}	30	—		30	—		-	$V_{ce} = 5 \text{ V}, \text{ I}_{c} = 500 \text{ mA}^{*1}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	_	1		_	1	V	$I_c = 500 \text{ mA},$ $I_B = 50 \text{ mA}^{*1}$
Base to emitter voltage	V_{BE}	_	—	1.5	_	—	1.5	V	$V_{ce} = 5 \text{ V}, \text{ I}_{c} = 150 \text{ mA}^{*1}$
Gain bandwidth product	f_{T}	_	180	—	_	180		MHz	$V_{ce} = 5 \text{ V}, \text{ I}_{c} = 150 \text{ mA}^{*1}$
Collector output capacitance	Cob	—	14		—	14		pF	$V_{CB} = 10 \text{ V}, \text{ I}_{E} = 0,$ f = 1 MHz

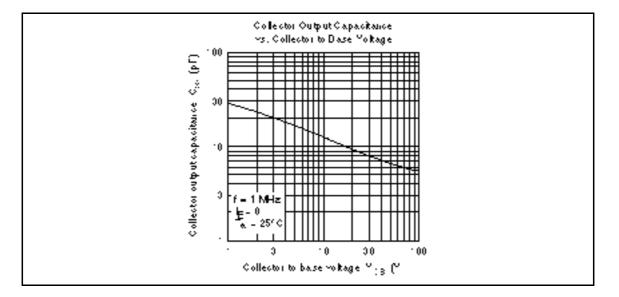
Notes: 1. Pulse test

2. The 2SD2122(L)/(S) and 2SD2123(L)/(S) are grouped by $h_{\mbox{\scriptsize FE1}}$ as follows.

В	С
60 to 120	100 to 200







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